



PSMN013-100XS

N-channel 100V 13 m Ω standard level MOSFET in TO220F (SOT186A)

Rev. 1 — 13 December 2011

Preliminary data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220F (SOT186A) package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Isolated package
- Suitable for standard level gate drive

1.3 Applications

- AC-to-DC power supply equipment
- Server power supplies
- Motor control
- Synchronous rectification

1.4 Quick reference data

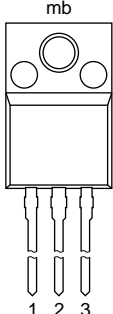
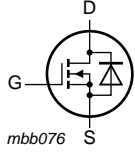
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$; $T_j \leq 175\text{ }^\circ\text{C}$	-	-	100	V
I_D	drain current	$T_{mb} = 25\text{ }^\circ\text{C}$; $V_{GS} = 10\text{ V}$; see Figure 1	-	-	35.2	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$; see Figure 2	-	-	48.4	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 10\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 12 ; see Figure 13	-	10.8	13.9	m Ω
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 10\text{ A}$; $V_{DS} = 50\text{ V}$; see Figure 14 ; see Figure 15	-	17.5	-	nC
$Q_{G(tot)}$	total gate charge		-	57.5	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ }^\circ\text{C}$; $I_D = 35.2\text{ A}$; $V_{sup} \leq 100\text{ V}$; unclamped; $R_{GS} = 50\text{ }\Omega$; see Figure 3	-	-	180	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb		mounting base; isolated		

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

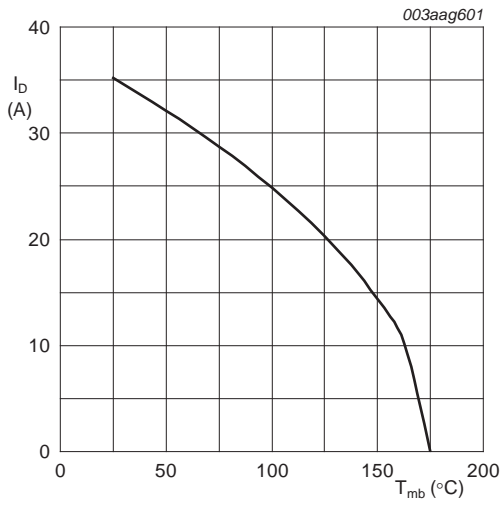
Type number	Package		
	Name	Description	Version
PSMN013-100XS	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

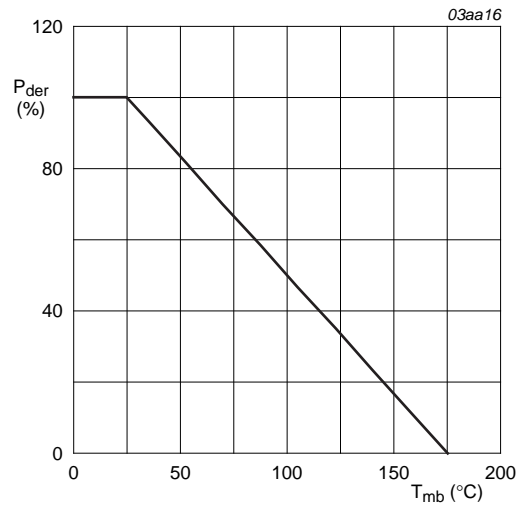
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$; see Figure 1	-	35.2	A
		$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$; see Figure 1	-	24.9	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 4	-	141	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	48.4	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	40.3	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	141	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 35.2\text{ A}; V_{sup} \leq 100\text{ V}; \text{unclamped}; R_{GS} = 50\text{ }\Omega$; see Figure 3	-	180	mJ



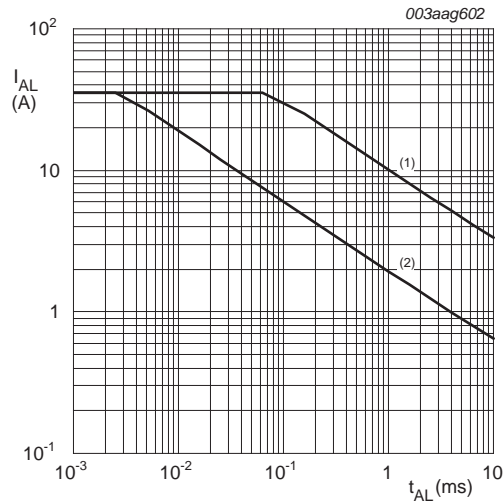
$$V_{GS} \geq 10V$$

Fig 1. Continuous drain current as a function of mounting base temperature



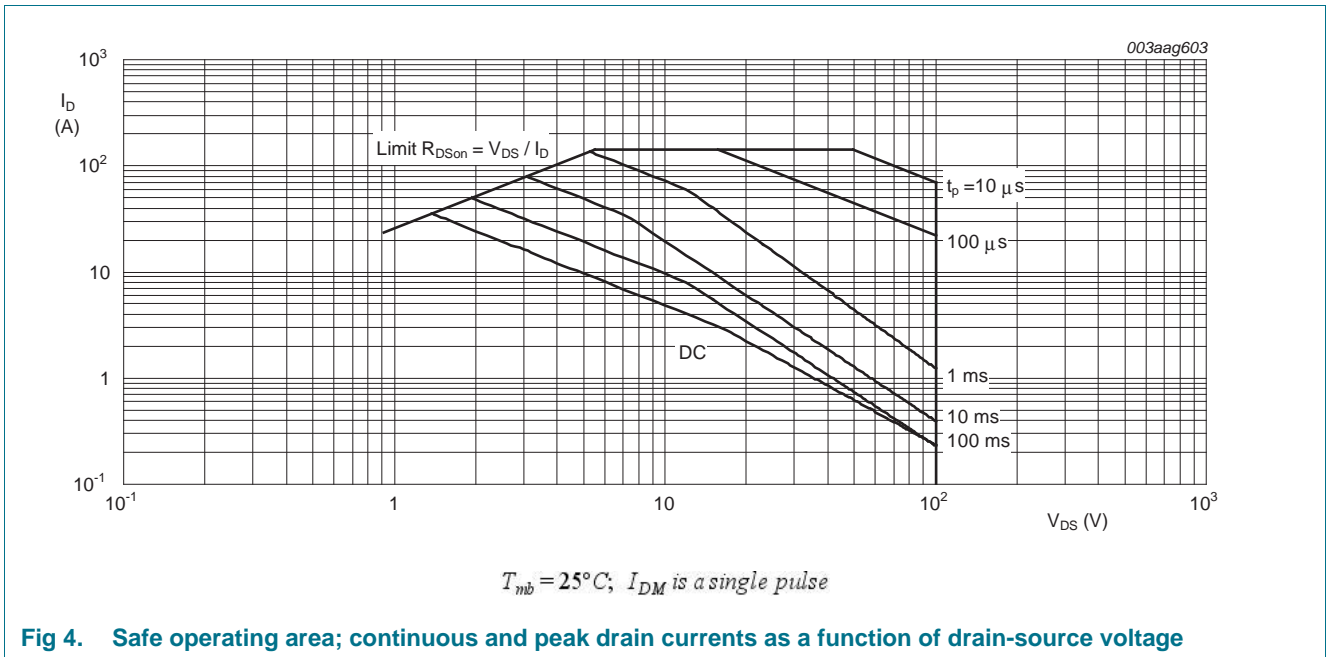
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.85	3.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	55	-	K/W

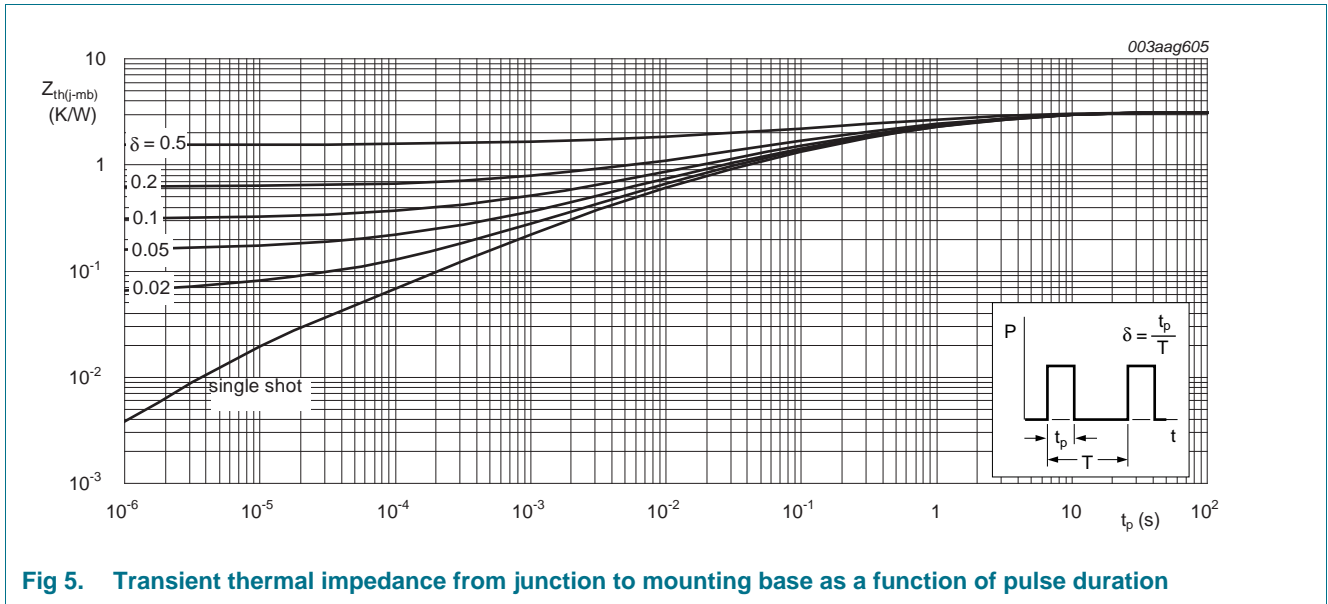


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{isol}	isolation capacitance	$f = 1 \text{ MHz}$	-	10	-	pF
$V_{isol(RMS)}$	RMS isolation voltage	$50 \text{ Hz} \leq f \leq 60 \text{ Hz}$; $RH \leq 65 \%$; sinusoidal waveform; clean and dust free	-	-	2500	V

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	2	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 100 \text{ }^\circ\text{C}$	-	-	40	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13	-	10.8	13.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see Figure 13	-	18.9	24.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 13	-	30.2	38.9	mΩ
R_G	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15	-	57.5	-	nC
Q_{GS}	gate-source charge		-	13.1	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	8.8	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	4.3	-	nC
Q_{GD}	gate-drain charge		-	17.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 10 \text{ A}; V_{DS} = 50 \text{ V};$ see Figure 14	-	4.5	-	V
C_{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16 ; see Figure 17	-	3195	-	pF
C_{oss}	output capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16	-	221	-	pF
C_{riss}	reverse transfer capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16 ; see Figure 17	-	136	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 5 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 4.7 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	18	-	ns
t_r	rise time		-	18	-	ns
$t_{d(off)}$	turn-off delay time		-	46	-	ns
t_f	fall time		-	21	-	ns

Table 7. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 10\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; see Figure 18	-	0.8	1.2	V
t_{rr}	reverse recovery time	$I_S = 10\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$;	-	52	-	ns
Q_r	recovered charge	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$	-	109	-	nC

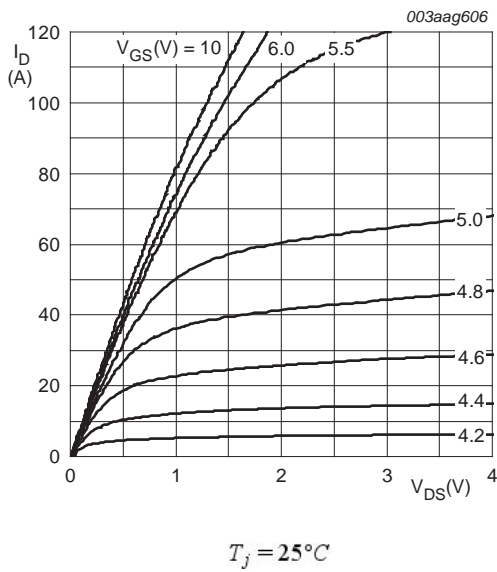


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

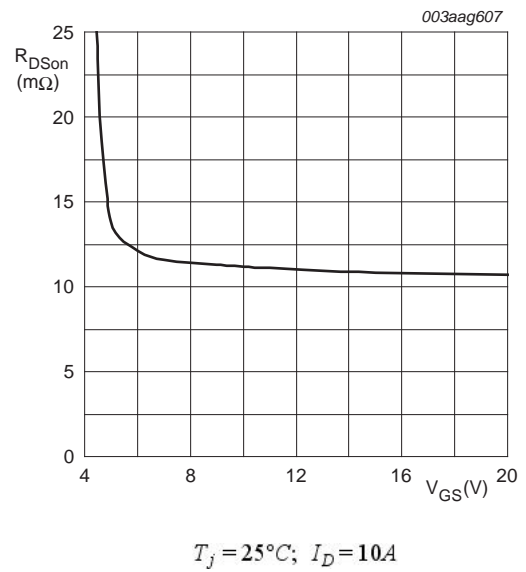


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

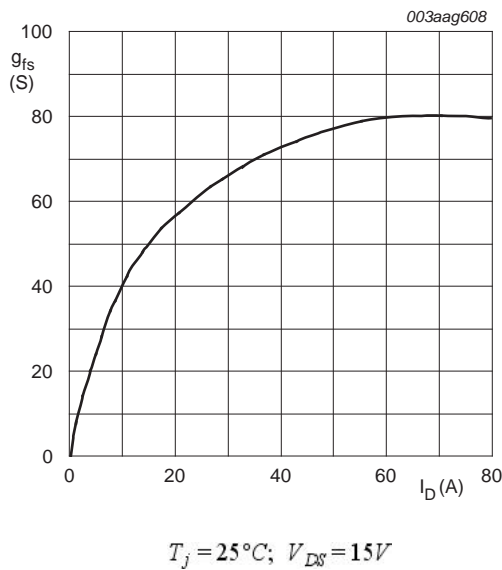


Fig 8. Forward transconductance as a function of drain current; typical values

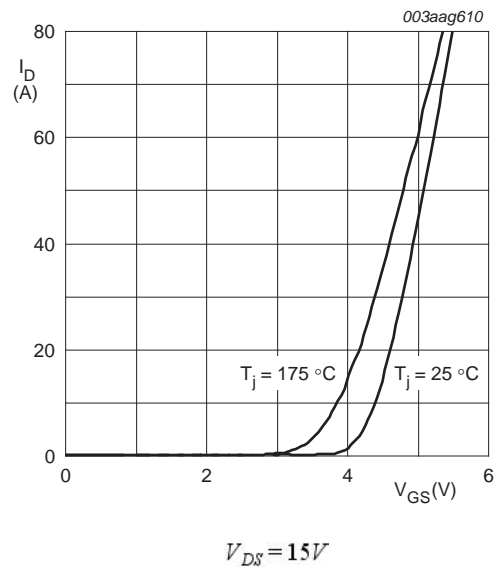
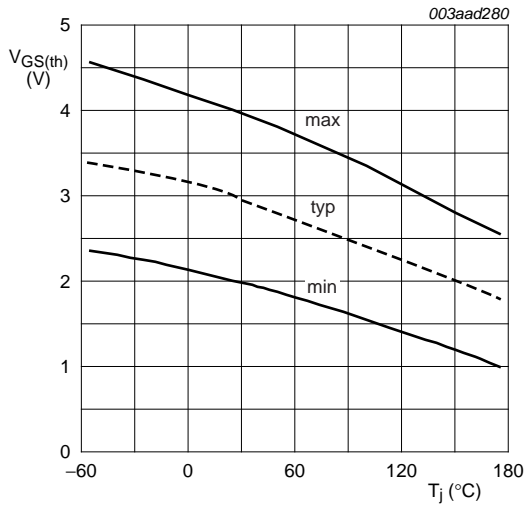
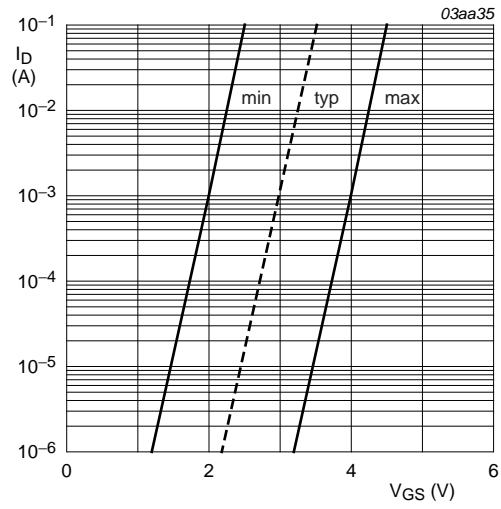


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



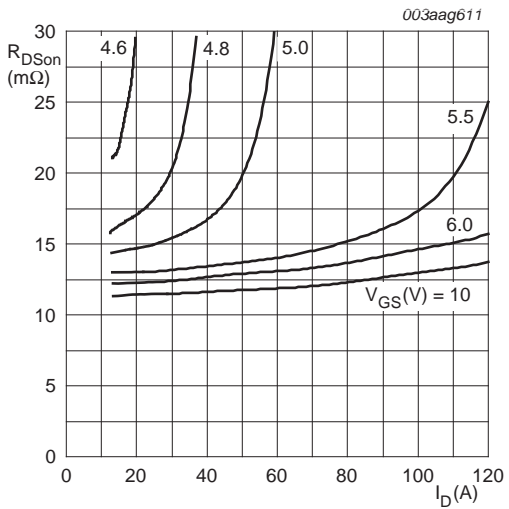
$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



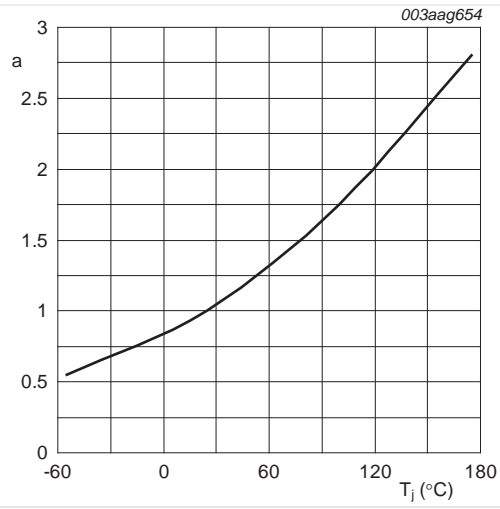
$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$T_j = 25^\circ\text{C}$$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

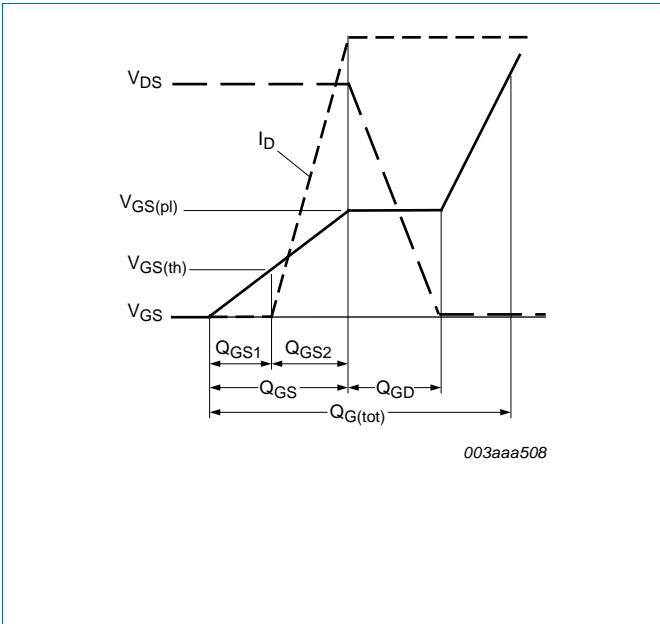


Fig 14. Gate charge waveform definitions

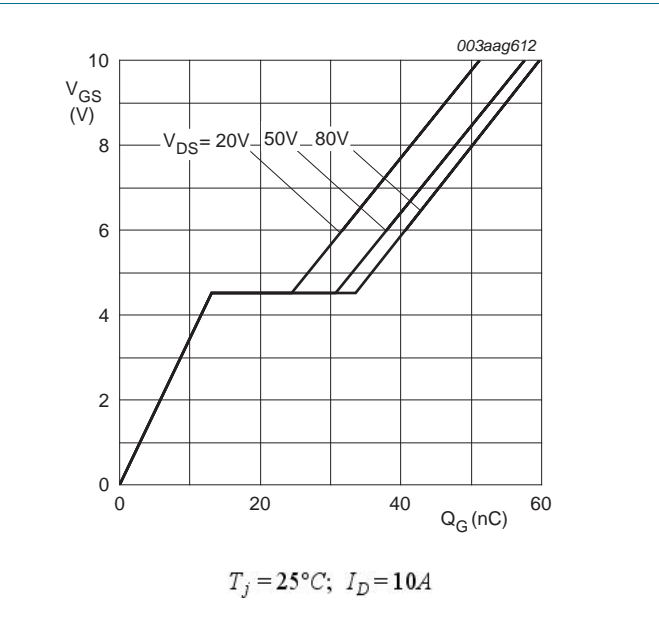


Fig 15. Gate-source voltage as a function of gate charge; typical values

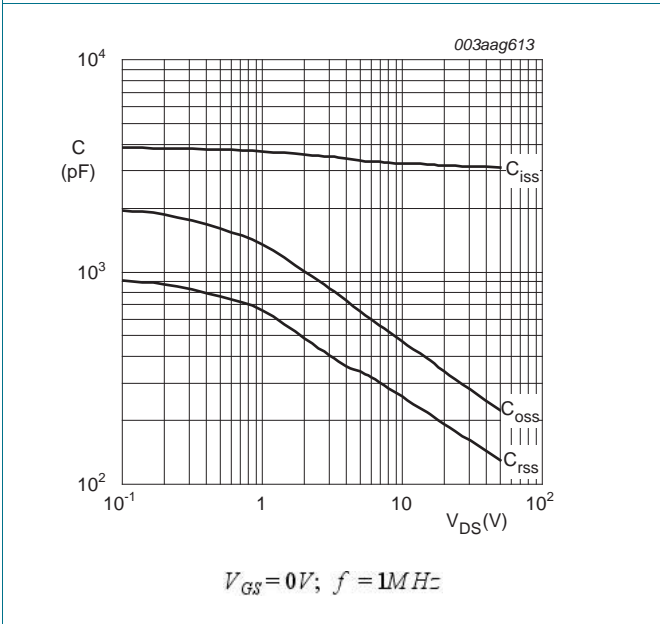


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

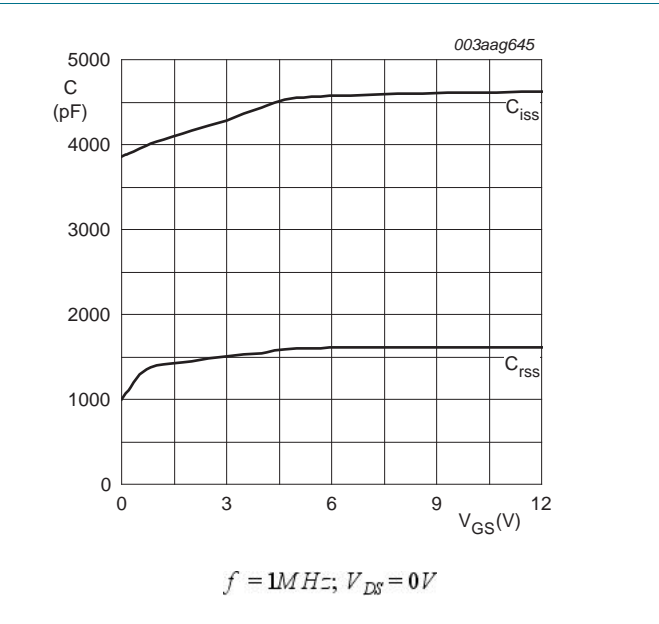


Fig 17. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

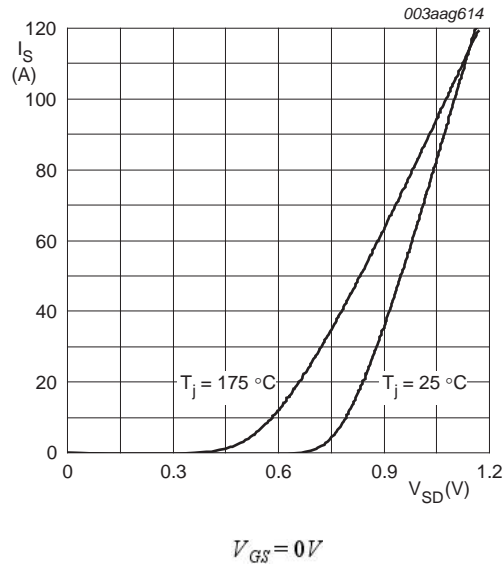


Fig 18. Source current as a function of source-drain voltage; typical values

8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

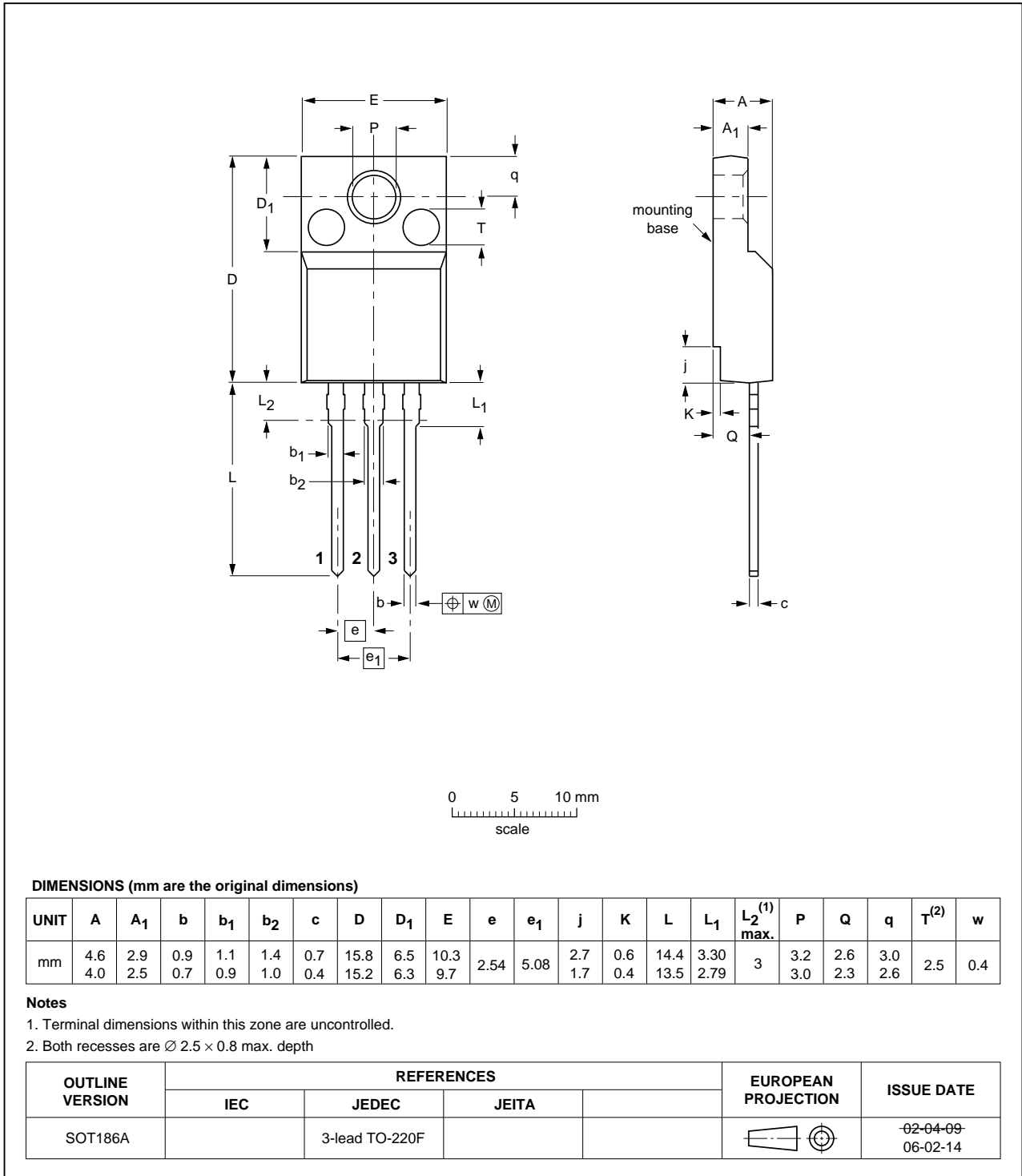


Fig 19. Package outline SOT186A (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-100XS v.1	20111213	Preliminary data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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